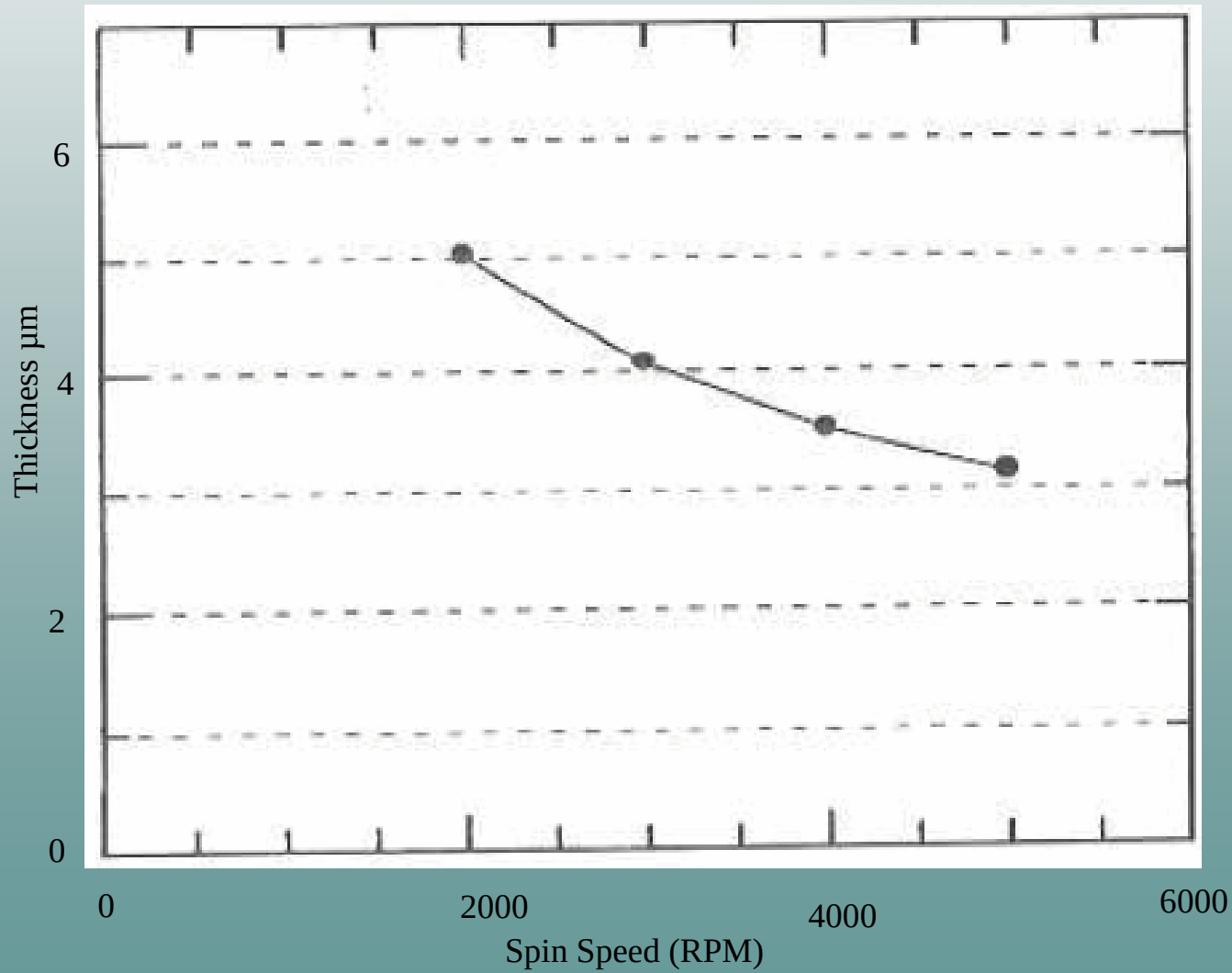
SIPR-3252-4.0
Posi-type Photoresist

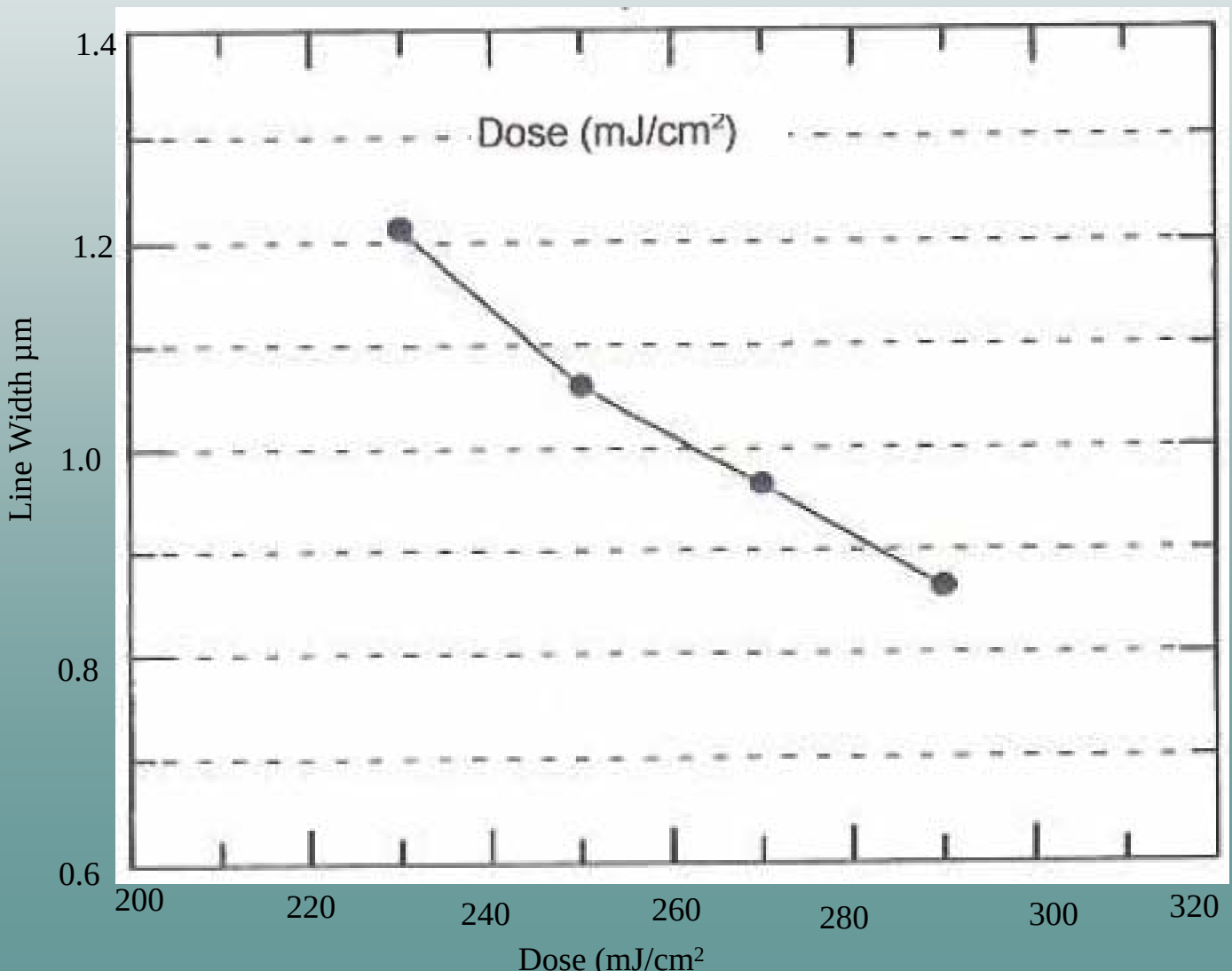
Substrate : Bare Si wafer, HMDS primed
Film Thickness:4.0µm Prebake: 100°Cx120 sec
Exp.: NSR-1755i7A , NA = 0.50
PEB: 110°C x 90 sec
Dev.: 50 sec x 2 puddles (SSFD-238 [TMAH = 2.38%])

Thickness vs Spin Speed

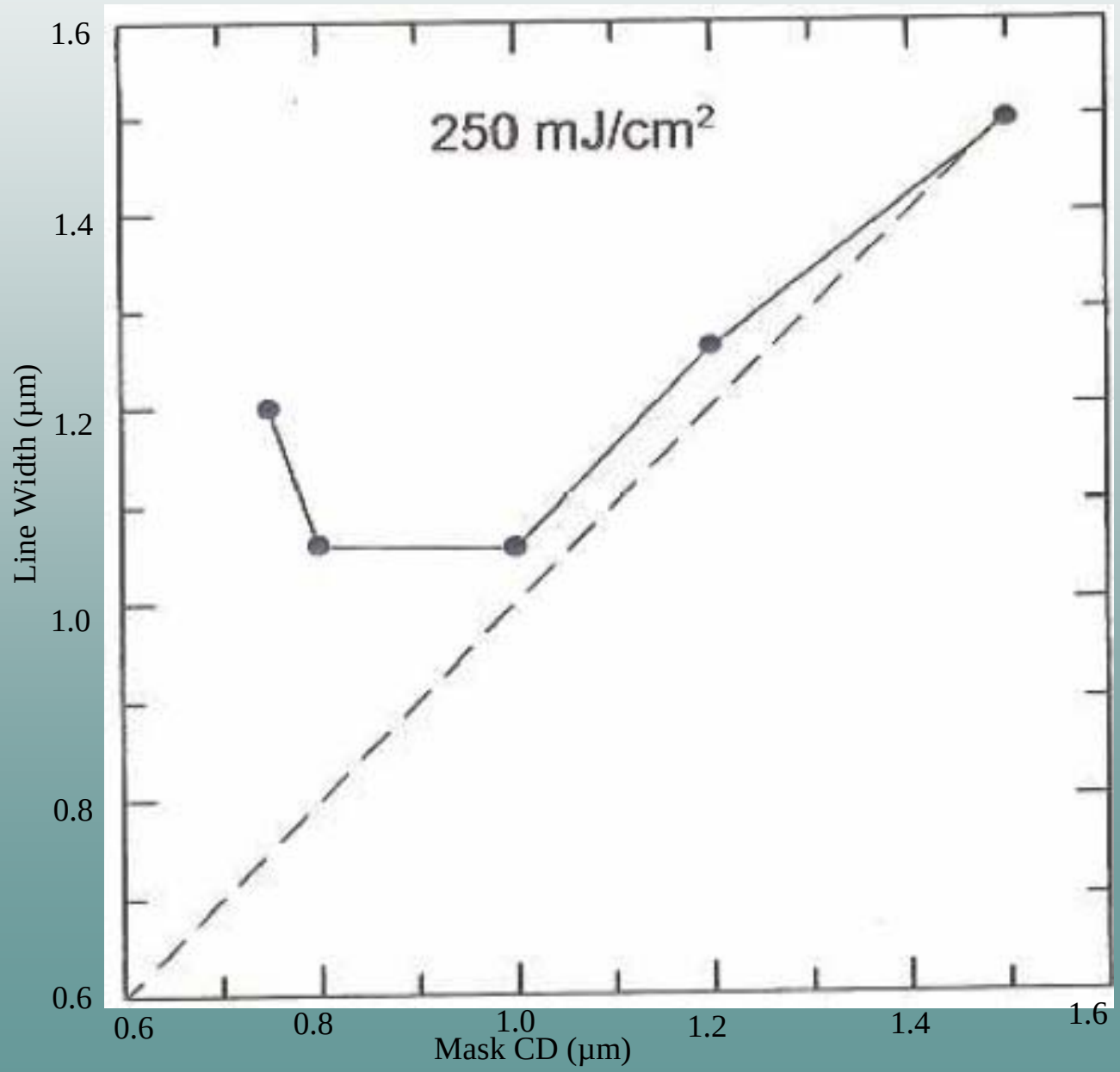


SIPR-3252-4.0

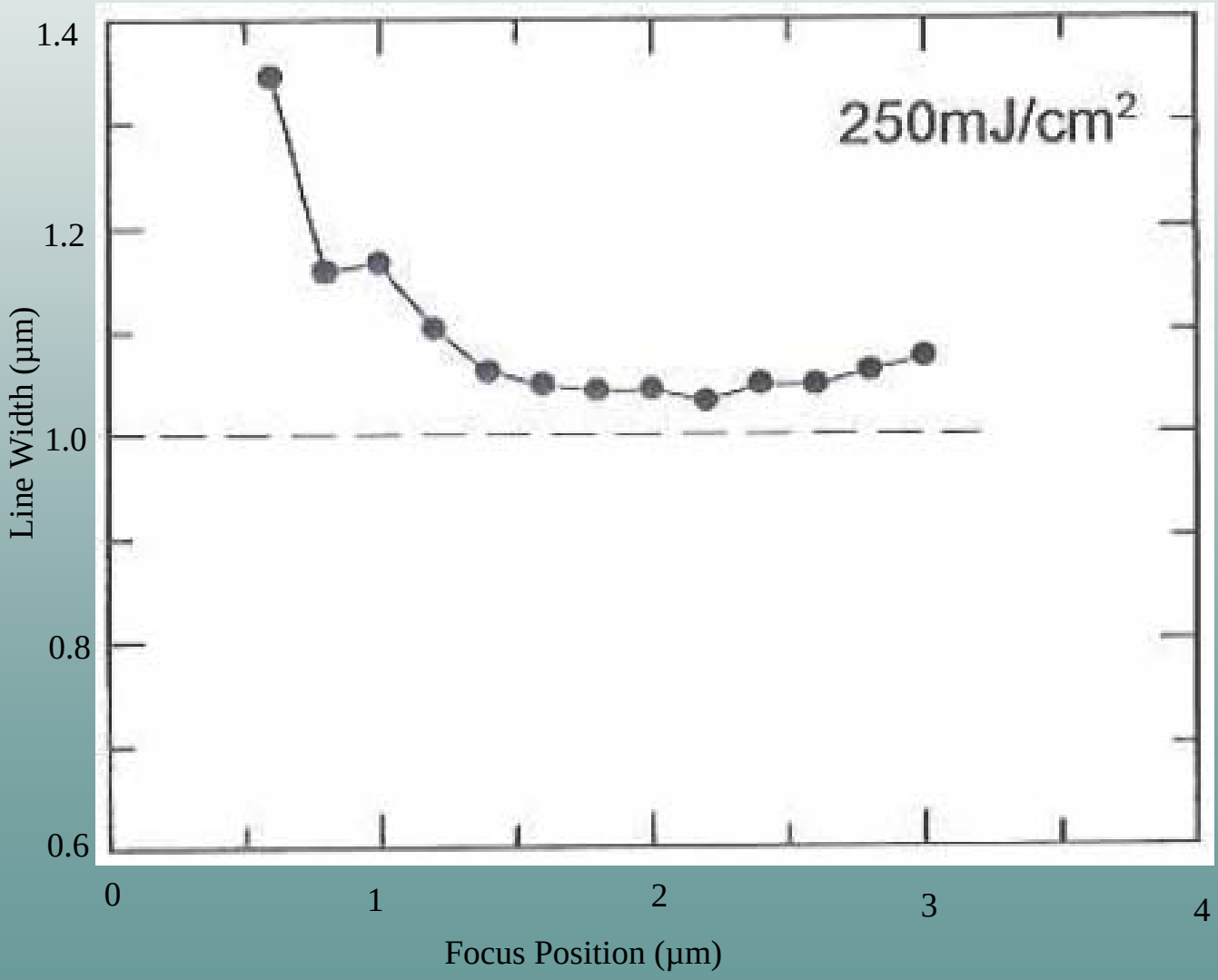
Exposure Latitude
1.0 µmL/S



Mask Linearity



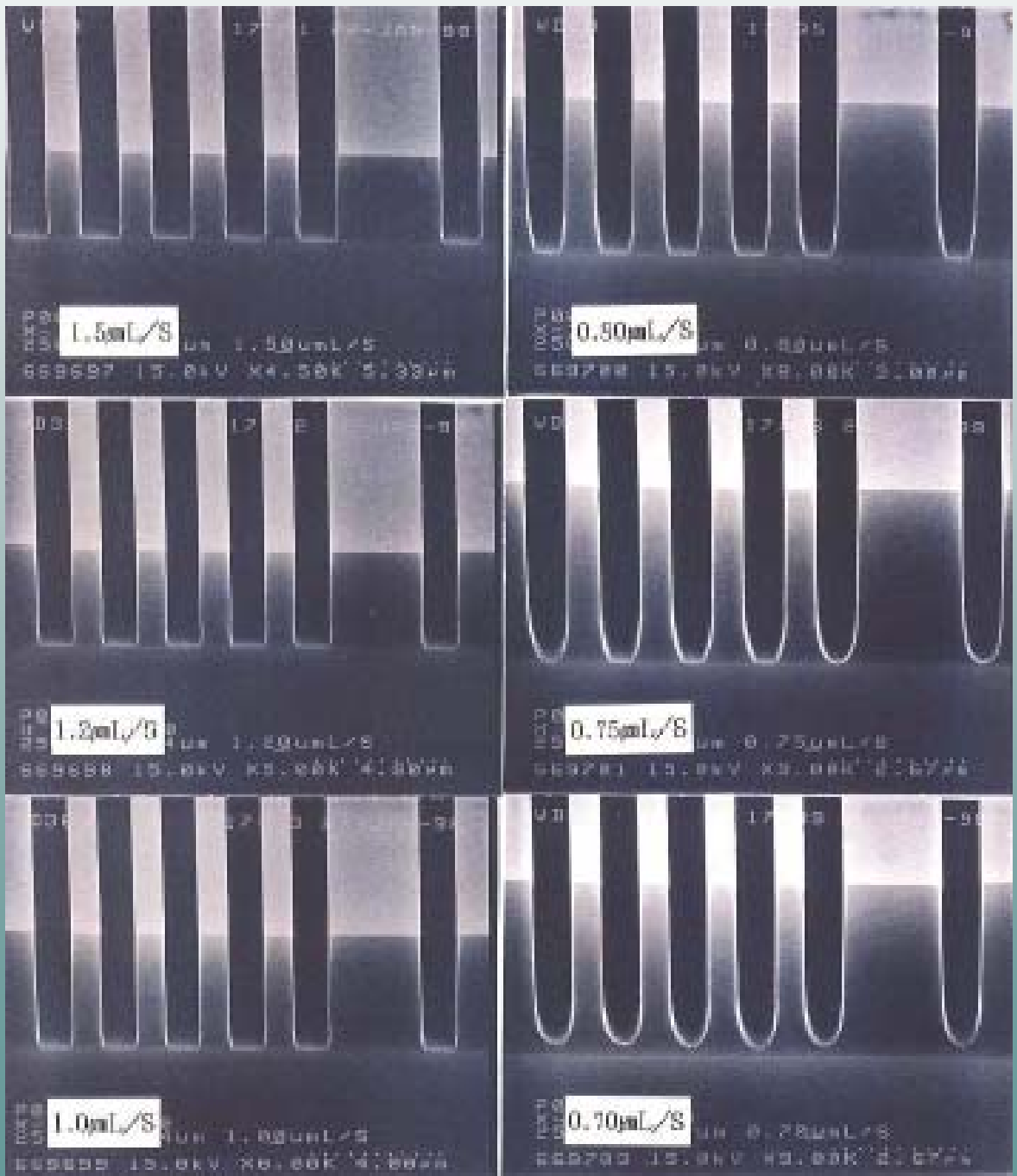
Depth of Focus
1.0 µm L/S



Mask Linearity

Bare Si wafer,
HMDS primed

Film Thickness:4.0µm Prebake: 100°Cx120 sec
Exp.: 250mJ/cm2 (NSR-1755iA NA = 0.50,
PEB: 1110°C x 90 sec
Dev.: 50 sec x 2 puddles (SSFD-238 [TMAH = 2.38%])



SIPR-3252-4.0
Depth of Focus
1.0 µm L/S

Bare Si wafer, HMDS primed

Film Thickness:4.0µm Prebake: 100°Cx120 sec
Exp.: 250mJ/cm2 (NSR-1755iA NA = 0.50)
PEB: 110°C x 90 sec
Dev.: 50 sec x 2 puddles (SSFD-238 [TMAH = 2.38%])

SIPR-3252-4.0
Depth of Focus
1.0 µm L/S

Continued